

YJ Planar Schottky Barrier Diode Die Specification

150V 1A, 32mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB032H150SS-280A

Main Products Characterstics

‡ \$YHUDJH IRUZDUG FXUUHQW ,) \$9 \$
‡ 0D[LPXP RSHUDWLQJ MXQFWLRQ WHPSHUDWXUH 7M f &
‡ (6' UDWLQJ !.9 SHU ,(& &RQWDFW 'LVFKDUJH
‡ 7RS PHWDO \$J

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

$I_F = 1\text{ A}$
 $3 \times 0 \text{ V H } 7 \text{ H V W } \text{ W } \leq 2\%$

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.
Recommended Storage Environment:
does not guarantee device performance after assembly.
Store in original container, in dessicated nitrogen, with no contamination.
Operating temperature range: -55°C to 175°C (x-none)
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